NSN 5962-01-351-7275

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View Online at https://aerobasegroup.com/nsn/5962-01-351-7275

Overall Length:
1.290 inches
Overall Height:
0.425 inches
Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
Between 0.150 inches and 0.210 inches
Maximum Power Dissipation Rating:
320.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Satellite communications terminal an/usc-3 (v) 1
Features Provided:
Monolithic and static operation and electrostatic sensitive and hermetically sealed and w/disable
Inclosure Material:
Ceramic
Ceramic Inclosure Configuration:
Inclosure Configuration:
Inclosure Configuration: Dual-in-line
Inclosure Configuration: Dual-in-line Output Logic Form:
Inclosure Configuration: Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic
Inclosure Configuration: Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern:
Inclosure Configuration: Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 21 input
Inclosure Configuration: Dual-in-line Output Logic Form: Complementary-metal oxide-semiconductor logic Input Circuit Pattern: 21 input Case Outline Source And Designator:
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:40.00 milliamperes reverse current, dc absolute
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:40.00 milliamperes reverse current, dc absoluteTerminal Surface Treatment:
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:40.00 milliamperes reverse current, dc absoluteTerminal Surface Treatment:Solder
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:40.00 milliamperes reverse current, dc absoluteTerminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:40.00 milliamperes reverse current, dc absoluteTerminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:-0.5 volts power source and 8.0 volts power source
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:40.00 milliamperes reverse current, dc absoluteTerminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:-0.5 volts power source and 8.0 volts power sourceCapitance Rating Per Characteristic:
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:40.00 milliamperes reverse current, dc absoluteTerminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:-0.5 volts power source and 8.0 volts power sourceCapitance Rating Per Characteristic:10.00 input picofarads and 7.00 output picofarads
Inclosure Configuration:Dual-in-lineOutput Logic Form:Complementary-metal oxide-semiconductor logicInput Circuit Pattern:21 inputCase Outline Source And Designator:D-3 mil-m-38510Current Rating Per Characteristic:40.00 milliamperes reverse current, dc absoluteTerminal Surface Treatment:SolderVoltage Rating And Type Per Characteristic:-0.5 volts power source and 8.0 volts power sourceCapitance Rating Per Characteristic:10.00 input picofarads and 7.00 output picofaradsTime Rating Per Chacteristic:

Ram

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Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

24 printed circuit

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

Yes - demil/mli

Fiig:

A458a0